

(use as many sheets as necessary)

Sheet	A1	of	A1
-------	----	----	----

Sheet	A1	of	A1
-------	----	----	----

Application Number	10/560,488
Filing Date	December 12, 2005
First Named Inventor	Gerald Lucovsky
Confirmation No.	3119
Examiner Name	Benjamin P. Sandvik
Attorney Docket Number	5051-639

[illegible][illegible]

Examiner Initials*	Cite No.	Include name the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial), symposium, catalog, etc., date, page(s), volume- issue number(s), publisher, city and/or country where published	T
	2.	Woo Sik Kim: <i>Ferroelectric-gate field effect transistors using <math>\text{Nd}_2\text{Ti}_2\text{O}_7/\text{Y}_2\text{O}_3/\text{Si}</math> structures; Thin Solid Films 398-399 (2001) 663-667.</i>	
	3.	Seung-Gu Lim; <i>Dielectric functions and optical bandgaps of high-K dielectrics for metal-oxide-semiconductor field-effect transistors by far ultraviolet spectroscopic ellipsometry; Journal of Applied Physics, Volume: 91, Number 7, pp 4500-4505 (April 1, 2002).</i>	
	4.	J. K. Yamamoto, <i>Microwave dielectric properties of layered perovskite <math>\text{A}_2\text{B}_2\text{O}_7</math> single-crystal fibers; Elsevier Science Publishers B.V. (North-Holland (1991) Matenial Letters No. 11/12 pp 497-500.</i>	
	5.	European communication with European Search Report for Application No. 04776548.2 – 1235 PCT/US2004018663, dated 5-6-2008.	

Examiner Signature /Benjamin Sandvik/ (09/03/2008)

Date Considered

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if

not in conformance and not considered. include copy of this form with next communication to applicant